

FIG. 1

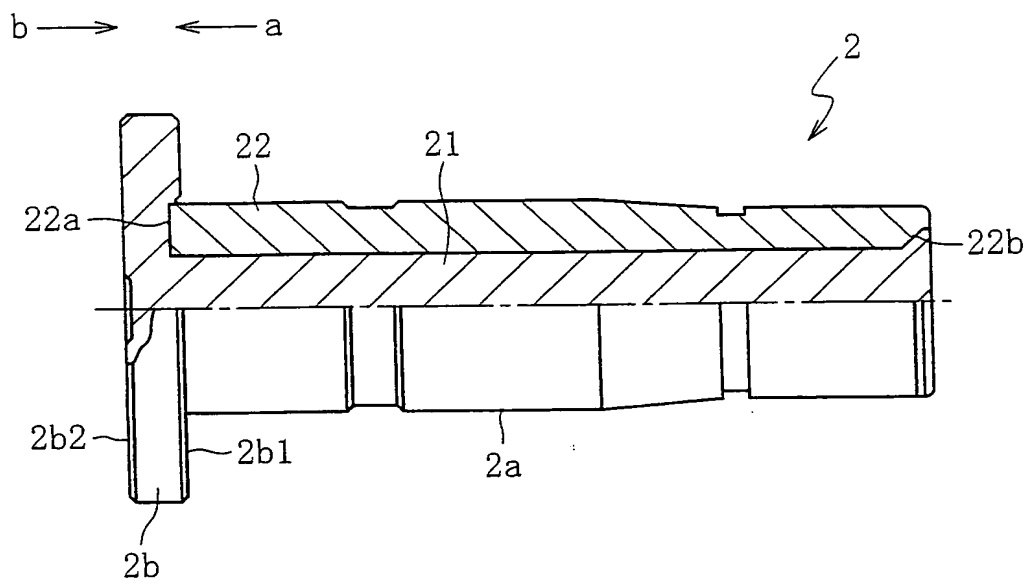
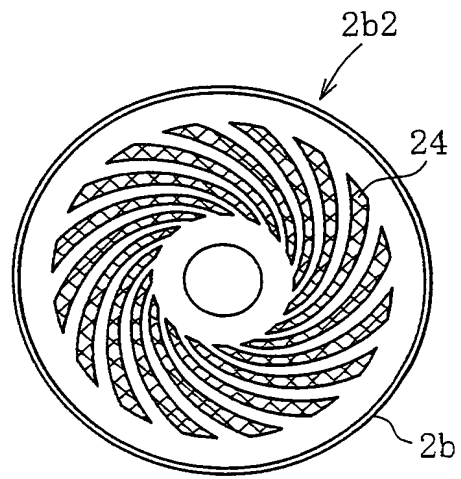
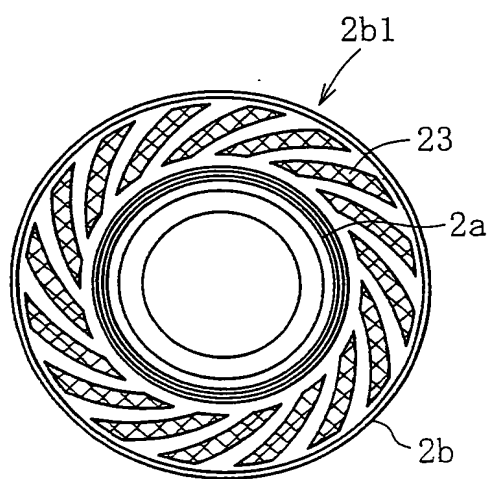


FIG. 2(a)

FIG. 2(b)



This cross-sectional view shows a semiconductor device. A central layer 2 is positioned on a base 1. Layer 2 is flanked by regions 7 and 10. Below layer 2 is a layer 7c, which is further underlaid by a layer 2b. To the right of layer 2 is a region 8, followed by a layer 6. A layer 3 is located above region 8. Below region 8 is a layer 4, and below layer 4 is a layer 5. A dimension D is indicated on the right side of the device.

FIG. 5

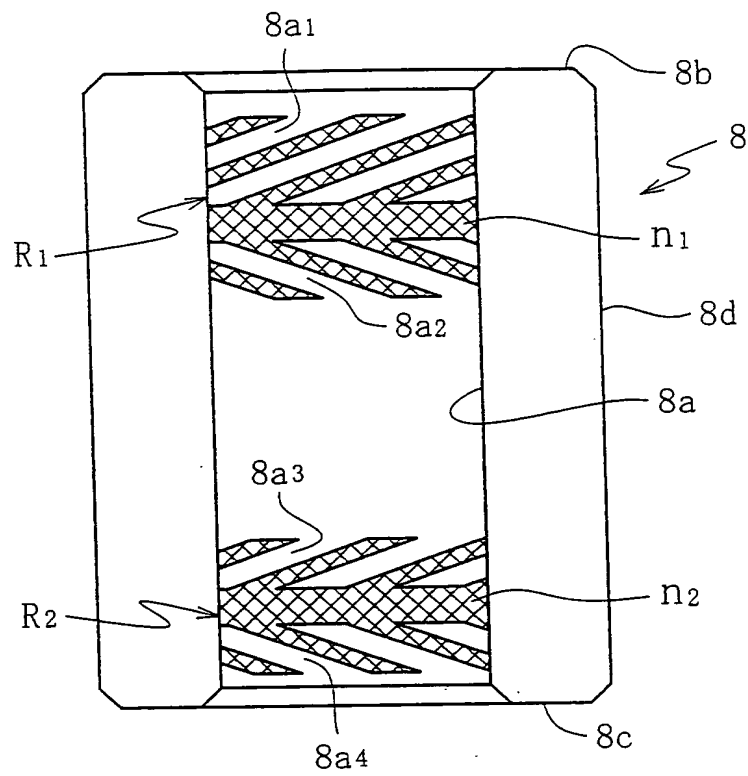


FIG. 6

